

Title (en)
LOW-INDUCTANCE CONNECTING DEVICE FOR CONNECTING A SEMICONDUCTOR MODULE AND AN INTERMEDIATE CIRCUIT CAPACITOR

Title (de)
NIEDERINDUKTIVE VERBINDUNGSVORRICHTUNG ZUM VERBINDEN EINES HALBLEITERMMODULS UND EINES ZWISCHENKREISKONDENSATORS

Title (fr)
DISPOSITIF DE CONNEXION À FAIBLE INDUCTANCE POUR CONNECTER UN MODULE SEMI-CONDUCTEUR ET UN CONDENSATEUR DE CIRCUIT INTERMÉDIAIRE

Publication
EP 3900036 A1 20211027 (DE)

Application
EP 19809767 A 20191125

Priority

- DE 102018222017 A 20181218
- DE 102019202777 A 20190301
- EP 2019082337 W 20191125

Abstract (en)
[origin: WO2020126316A1] Low-inductance connecting device (10) for connecting a semiconductor module (20) to an intermediate circuit capacitor (30), comprising at least one first contact region (11a) and one second contact region (12) which has opposite polarity to the first contact region (11a), which first and second contact region are designed to make contact with the semiconductor module (20), at least one third contact region (13a) which has the same polarity as the first contact region (11a) and one fourth contact region (14) which has opposite polarity to the third contact region (13a), which third and fourth contact regions are designed to make contact with the intermediate circuit capacitor (30), at least one first connecting region (15a) which is designed to connect the first contact region (11a) and the third contact region (13a) to one another, and at least one second connecting region (16a) which is designed to connect the second contact region (12) and the fourth contact region (14) to one another, wherein the first connecting region (15a) and the second connecting region (16a) are each designed as planar busbars which are separate from one another.

IPC 8 full level
H01L 25/07 (2006.01); **H01G 4/228** (2006.01); **H02M 7/00** (2006.01)

CPC (source: EP US)
H01G 4/228 (2013.01 - EP US); **H01L 23/48** (2013.01 - EP); **H01L 23/49811** (2013.01 - EP US); **H01L 23/642** (2013.01 - US); **H02M 7/003** (2013.01 - EP US); **H05K 1/0231** (2013.01 - US)

Citation (search report)
See references of WO 2020126316A1

Designated contracting state (EPC)
AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

Designated extension state (EPC)
BA ME

DOCDB simple family (publication)
DE 102019202777 A1 20200618; CN 113169162 A 20210723; EP 3900036 A1 20211027; JP 2022515074 A 20220217; JP 7356503 B2 20231004; US 2022068777 A1 20220303; WO 2020126316 A1 20200625

DOCDB simple family (application)
DE 102019202777 A 20190301; CN 201980083899 A 20191125; EP 19809767 A 20191125; EP 2019082337 W 20191125; JP 2021534938 A 20191125; US 201917415032 A 20191125